



No.3794

2SC4441

NPN Triple Diffused Planar Silicon Transistor
 Very High-Definition Monocuro Display
 Horizontal Deflection Output Applications

Features

- High reliability(Adoption of HVP process).
- High fast.
- High breakdown voltage.
- Wide ASO.
- Adoption of MBIT process.
- Micaless package facilitating mounting.

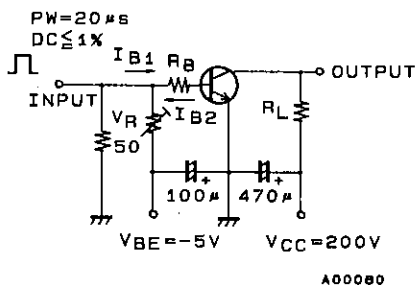
Absolute Maximum Ratings at Ta = 25°C

			unit
Collector-to-Base Voltage	V _{CB0}	600	V
Collector-to-Emitter Voltage	V _{CEO}	400	V
Emitter-to-Base Voltage	V _{EBO}	7	V
Collector Current	I _C	10	A
Peak Collector Current	i _{cp}	PW ≤ 300μs, Duty Cycle ≤ 10%	
Collector Dissipation	P _C	2.0	W
		T _c = 25°C	
Junction Temperature	T _j	35	W
Storage Temperature	T _{stg}	150	°C
		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Collector Cutoff Current	I _{CB0}	V _{CB} = 400V, I _E = 0			10	μA
	I _{CES}	V _{CE} = 600V			0.5	mA
Collector Sustain Voltage	V _{CEO(sus)}	I _C = 100mA, I _B = 0	400			V
Emitter Cutoff Current	I _{EBO}	V _{EB} = 5V, I _C = 0			1	mA
C-E Saturation Voltage	V _{CE(sat)}	I _C = 6A, I _B = 1.2A			0.8	V
B-E Saturation Voltage	V _{BE(sat)}	I _C = 6A, I _B = 1.2A			1.5	V
DC Current Gain	h _{FE(1)}	V _{CE} = 5V, I _C = 1.2A	15			
	h _{FE(2)}	V _{CE} = 5V, I _C = 6A	10		20	
Gain-Bandwidth Product	f _T	V _{CE} = 10V, I _C = 1.2A		20		MHz
Storage Time	t _{stg}	I _C = 7A, I _{B1} = 1.4A			3.0	μs
Fall Time	t _f	I _{B2} = -2.8A, R _L = 28.6Ω V _{CC} = 200V			0.2	μs

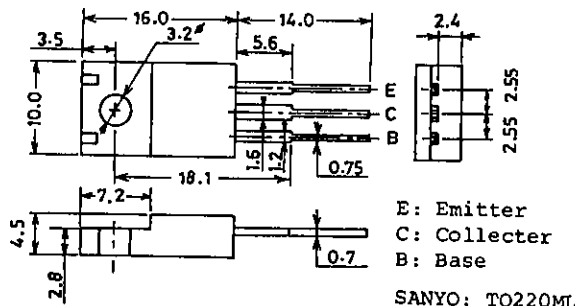
Switching Time Test Circuits

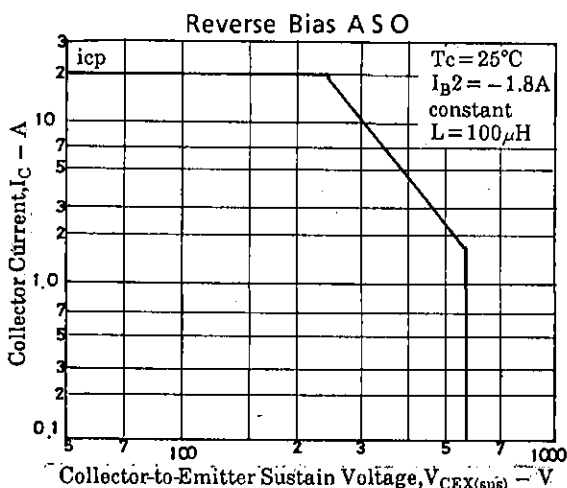
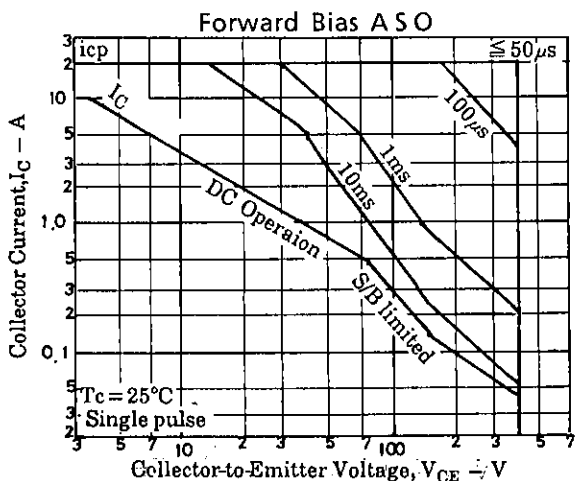
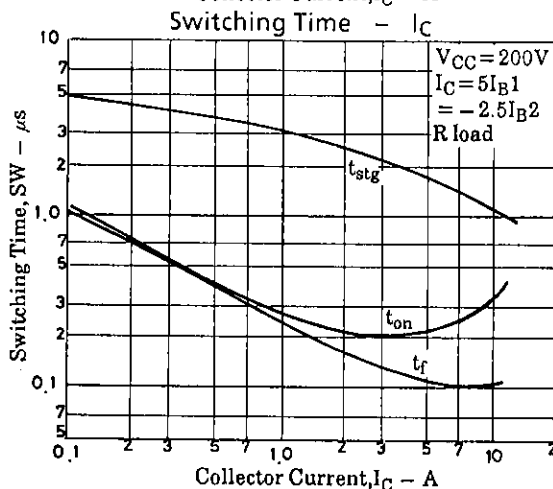
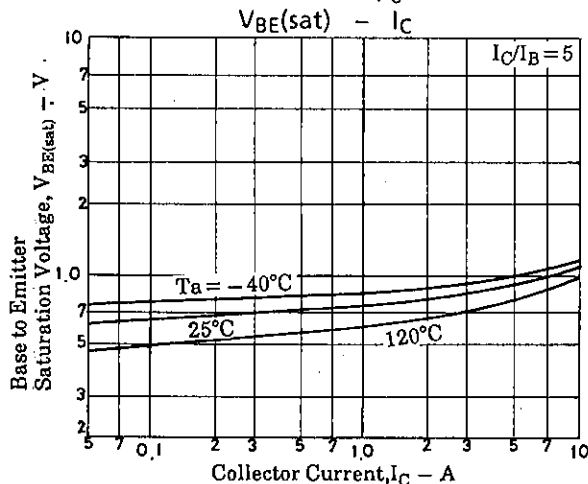
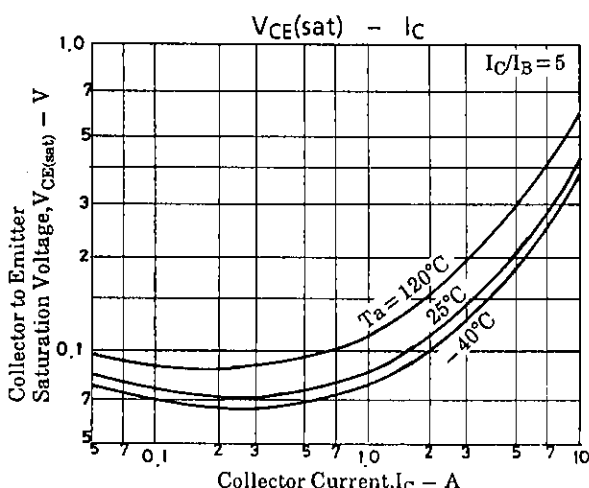
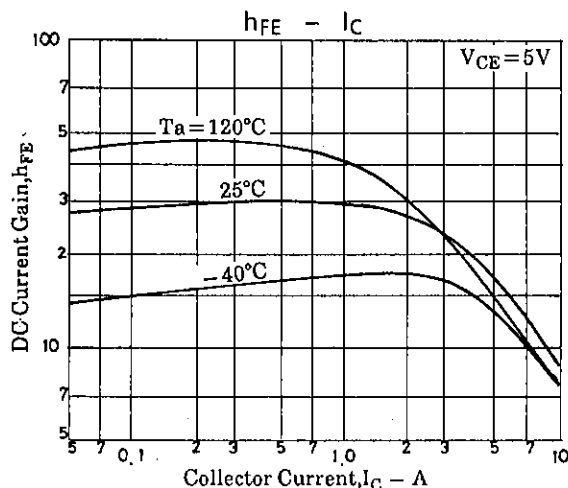
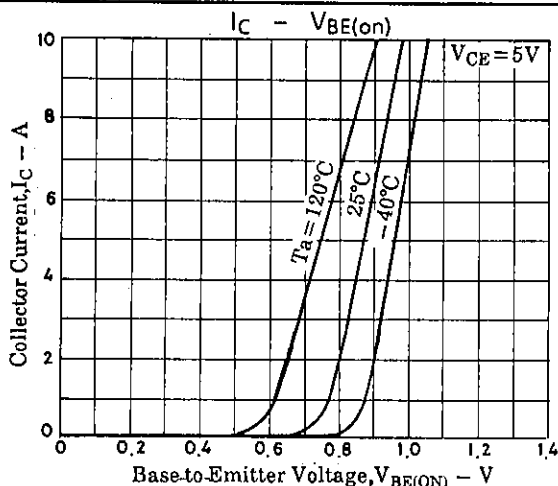
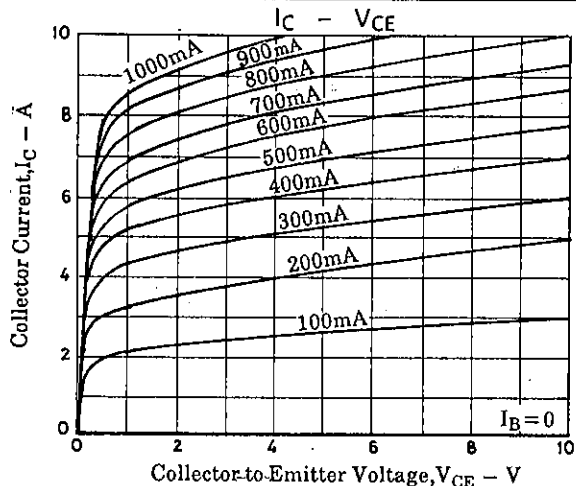


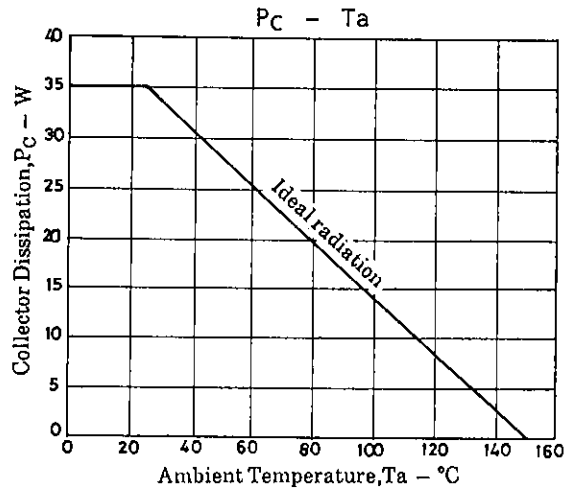
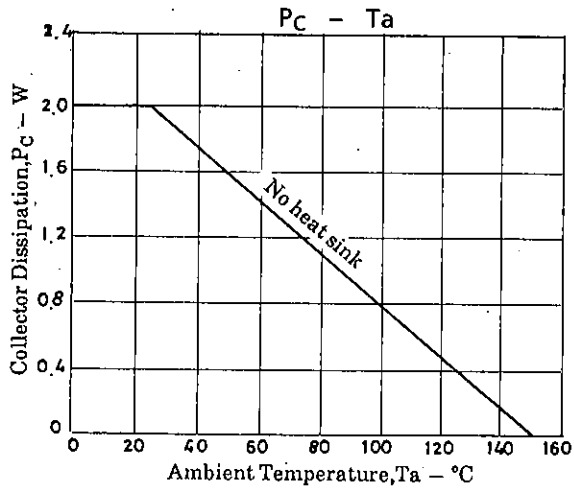
Unit (resistance:Ω, capacitance:F)

Package Dimensions

(unit: mm) 2041







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